

67,200-560
2001-0155

ABSTRACT

0041 A method is provided for improving a photolithographic patterning process in a dual damascene process by forming a resinous plug in a via opening to prevent out diffusion of nitrogen containing species from a low-k IMD layer in subsequent lithographic patterning and RIE etching processes to form a trench opening formed substantially over the via opening.

2001-0155-001